

Amendments to the Specification:

Please replace paragraph [0092] with the following rewritten paragraph:

[0092] The thickness of the monocrystalline silicon substrate 206a used in the bonding is, for example, about ~~600 nm~~ 600 μm . An oxide film layer 206b is formed in advance on a surface of the monocrystalline silicon substrate 206a, which is bonded to the substrate body 10A, and hydrogen ions (H^+) are implanted also in advance thereto, for example, with a dose of $10 \sim 10^{16}/\text{cm}^2$ and an accelerating voltage 100 keV. The oxide film layer 206b is formed by oxidizing the surface of the monocrystalline silicon substrate 206a by a thickness of about 0.05 to ~~0.8 nm~~ 0.8 μm .

Please replace paragraph [0094] with the following rewritten paragraph:

[0094] In order to further enhance a bonding strength, it is required that the heating temperature rises up to 450°C , but since a thermal expansion coefficient of the substrate body 10A made of quartz, etc. is largely different from a thermal expansion coefficient of the monocrystalline silicon substrate 206a, such heating causes defects, such as cracks in the monocrystalline silicon layer, so that the quality of the TFT array substrate 10 to be manufactured can deteriorate. In order to suppress the generation of defects, such as cracks, it is preferable that the monocrystalline silicon substrate 206a having been once subjected to the heating process of 300°C for the bonding ~~be made to be~~ to be made thinner to 100 to ~~150 nm~~ 150 nm by a wet etching or the CMP method and then is subjected to a higher-temperature heating process. For example, it is preferable that by etching the monocrystalline silicon substrate 206a to a thickness of ~~150 nm~~ 150 nm using a KOH aqueous solution of 80°C , bonding the etched substrate to the substrate body 10A, and then heating the bonded substrates again at a temperature of 450°C , the bonding strength be enhanced.